



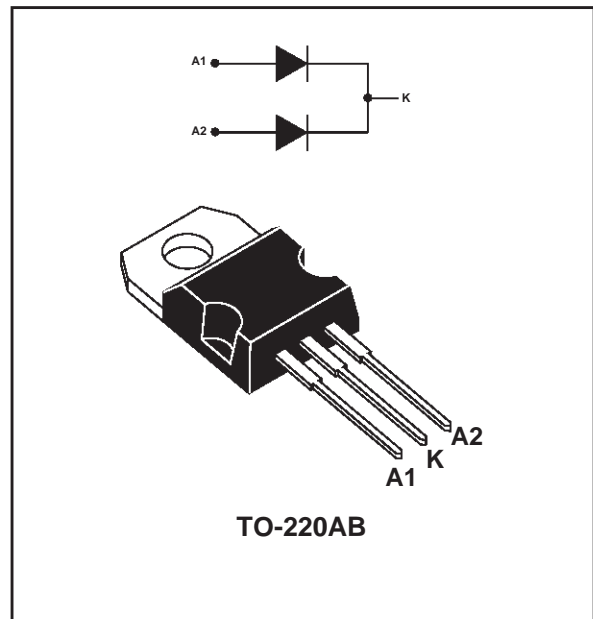
ULTRA-FAST RECOVERY RECTIFIER DIODES

MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 12 A
V_{RRM}	200 V
$T_j(\text{max})$	150°C
$V_F(\text{max})$	0.99 V
$t_{rr}(\text{max})$	30 ns

FEATURES

- SUITED FOR SMPS
- LOW LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIME
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY



Low cost dual center tap rectifier suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO-220AB, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

Symbol	Parameter		Value	Unit	
V_{RRM}	Repetitive peak reverse voltage		200	V	
$I_{F(RMS)}$	RMS forward current		30	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	$T_c = 115^\circ\text{C}$	Per diode	12	A
			Per device	24	
I_{FSM}	Surge non repetitive forward current		$T_p = 10\text{ ms}$ Sinusoidal	120	A
T_{stg}	Storage temperature range		- 65 to + 150	°C	
T_j	Maximum operating junction temperature		+ 150		

STPR2420CT

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	2.5	°C/W
		Total	1.4	
$R_{th(c)}$		Coupling	0.23	

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameters	Test conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			50	μA
		$T_j = 100^\circ\text{C}$				0.8	mA
V_F^{**}	Forward voltage drop	$T_j = 125^\circ\text{C}$	$I_F = 12\text{ A}$			0.99	V
		$T_j = 125^\circ\text{C}$	$I_F = 24\text{ A}$			1.20	
		$T_j = 25^\circ\text{C}$	$I_F = 24\text{ A}$			1.25	

Pulse test : * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.78 \times I_{F(AV)} + 0.0175 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Test conditions			Min.	Typ.	Max.	Unit
t_{rr}	$T_j = 25^\circ\text{C}$	$I_F = 0.5\text{ A}$	$I_{rr} = 0.25\text{ A}$ $I_R = 1\text{ A}$			30	ns
t_{fr}	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$	$t_r = 10\text{ ns}$ $V_{FR} = 1.1 \times V_F$		20		
V_{FP}	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$	$t_r = 10\text{ ns}$		3		V

Fig. 1: Average forward power dissipation versus average forward current (per diode).

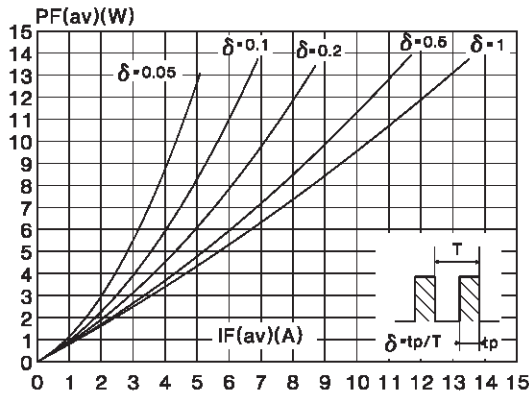


Fig. 2: Peak current versus form factor (per diode).

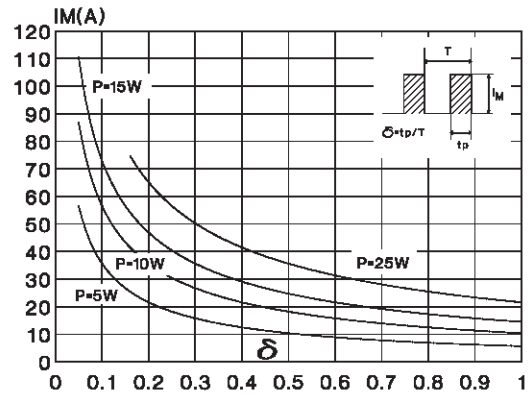


Fig. 3: Average current versus ambient temperature.

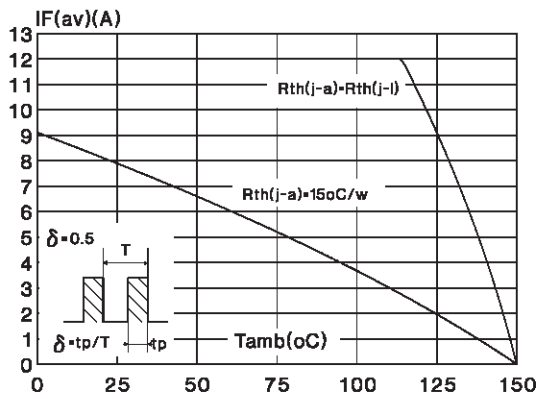


Fig. 4: Non repetitive surge peak forward current versus overload duration (maximum values).

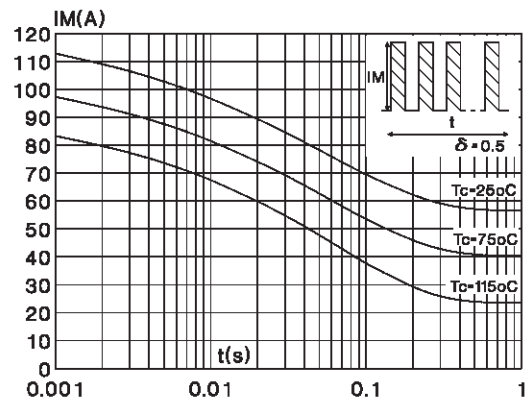


Fig. 5: Relative variation of thermal transient impedance junction to case versus pulse duration.

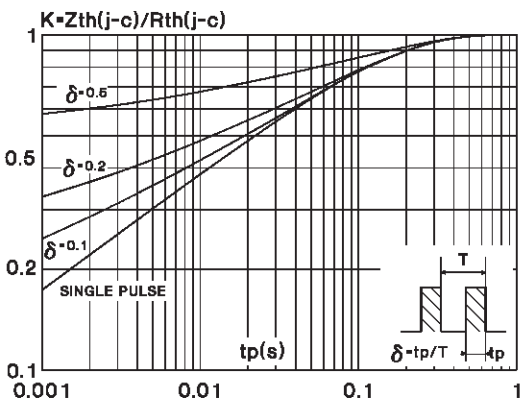


Fig. 6: Forward voltage drop versus forward current.

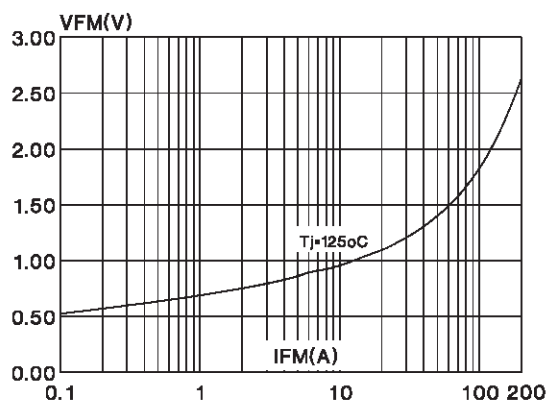


Fig. 7: Junction capacitance versus reverse voltage applied (typical values, per diode).

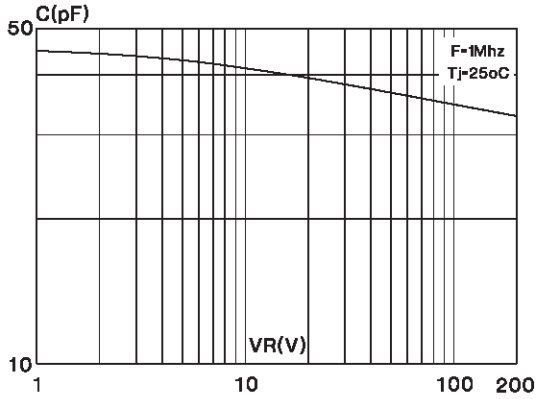


Fig. 8: Recovery charge versus dI_F/dt (per diode).

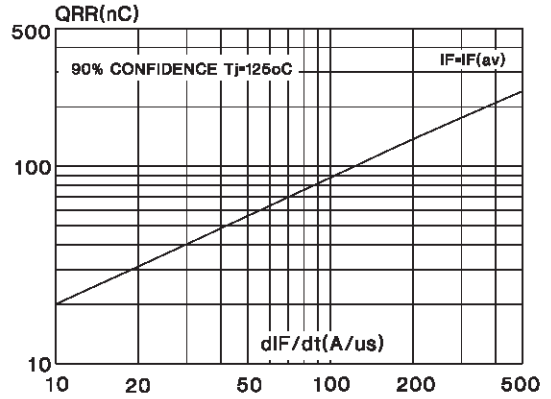


Fig. 9: Peak reverse current versus dI_F/dt (per diode).

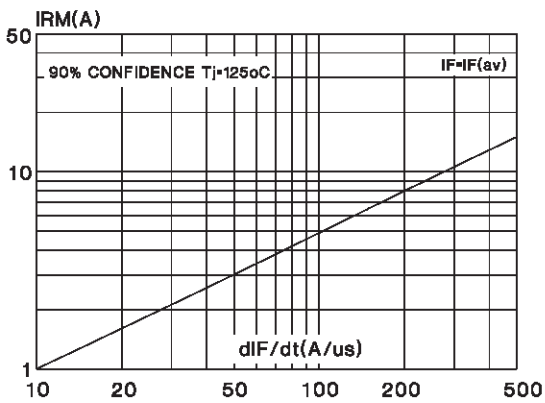
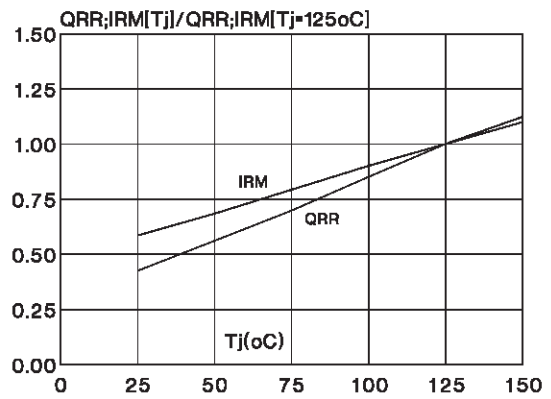
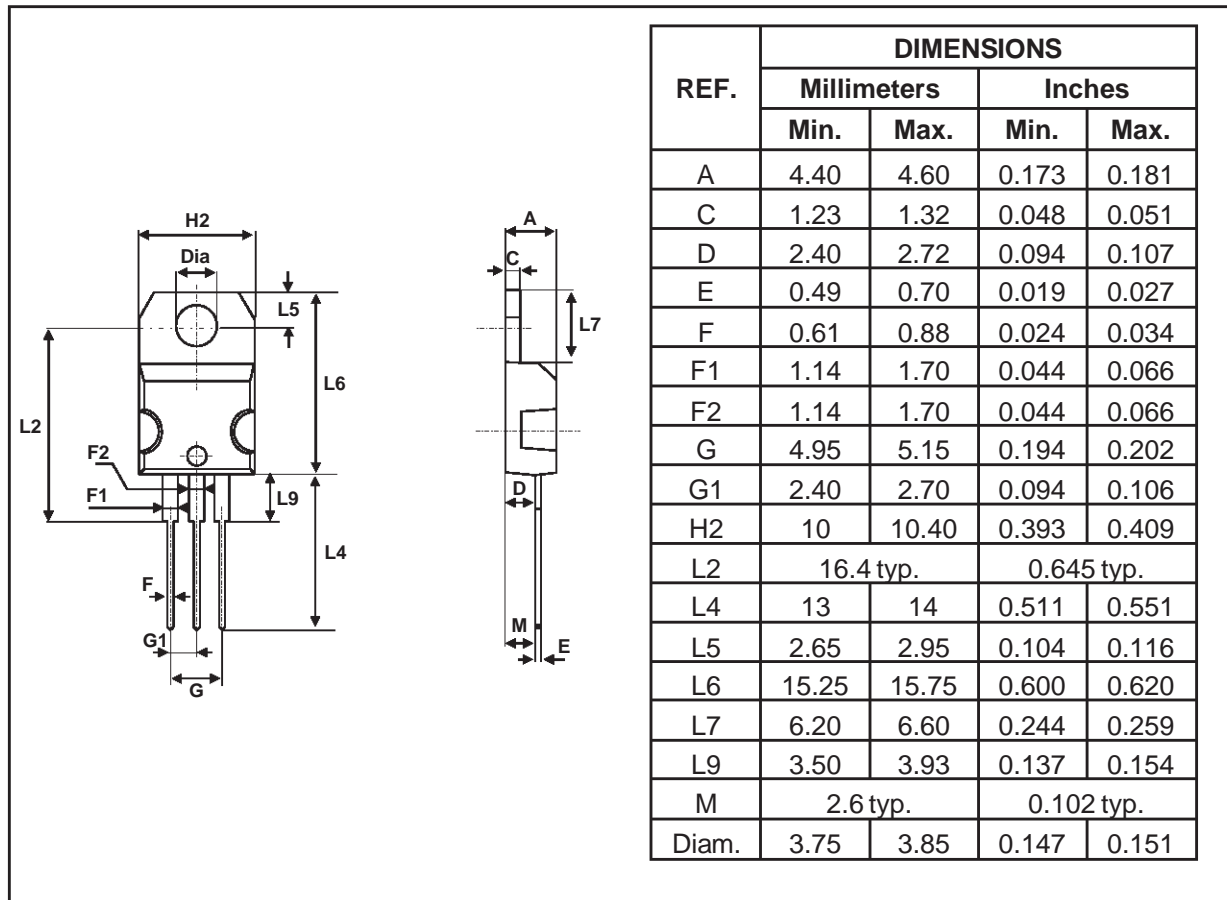


Fig. 10: Dynamic parameters versus junction temperature (per diode).



PACKAGE MECHANICAL DATA

TO-220AB



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